

Silicon PNP Power Transistors

2SB713

DESCRIPTION

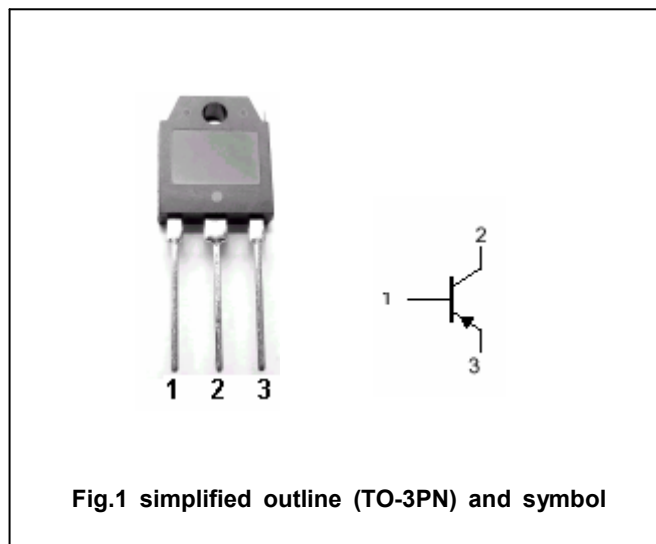
- With TO-3PN package
- Wide area of safe operation
- Excellent good linearity of h_{FE}

APPLICATIONS

- For high power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-140	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-9	A
I_{CP}	Collector current (Pulse)		-15	A
P_C	Collector power dissipation	$T_c=25^\circ\text{C}$	100	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-7A; I_B=-0.7A$			-2.0	V
V_{BE}	Base-emitter on voltage	$I_C=-7A; V_{CE}=-5V$			-1.8	V
I_{CBO}	Collector cut-off current	$V_{CB}=-140V; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3V; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-20mA; V_{CE}=-5V$	20			
h_{FE-2}	DC current gain	$I_C=-1A; V_{CE}=-5V$	40		200	
h_{FE-3}	DC current gain	$I_C=-7A; V_{CE}=-5V$	15			
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-5V$		7		MHz
C_{OB}	Collector output capacitance	$f=1MHz; V_{CB}=-10V$		220		pF

◆ h_{FE-2} Classifications

R	Q	P
40-80	60-120	100-200

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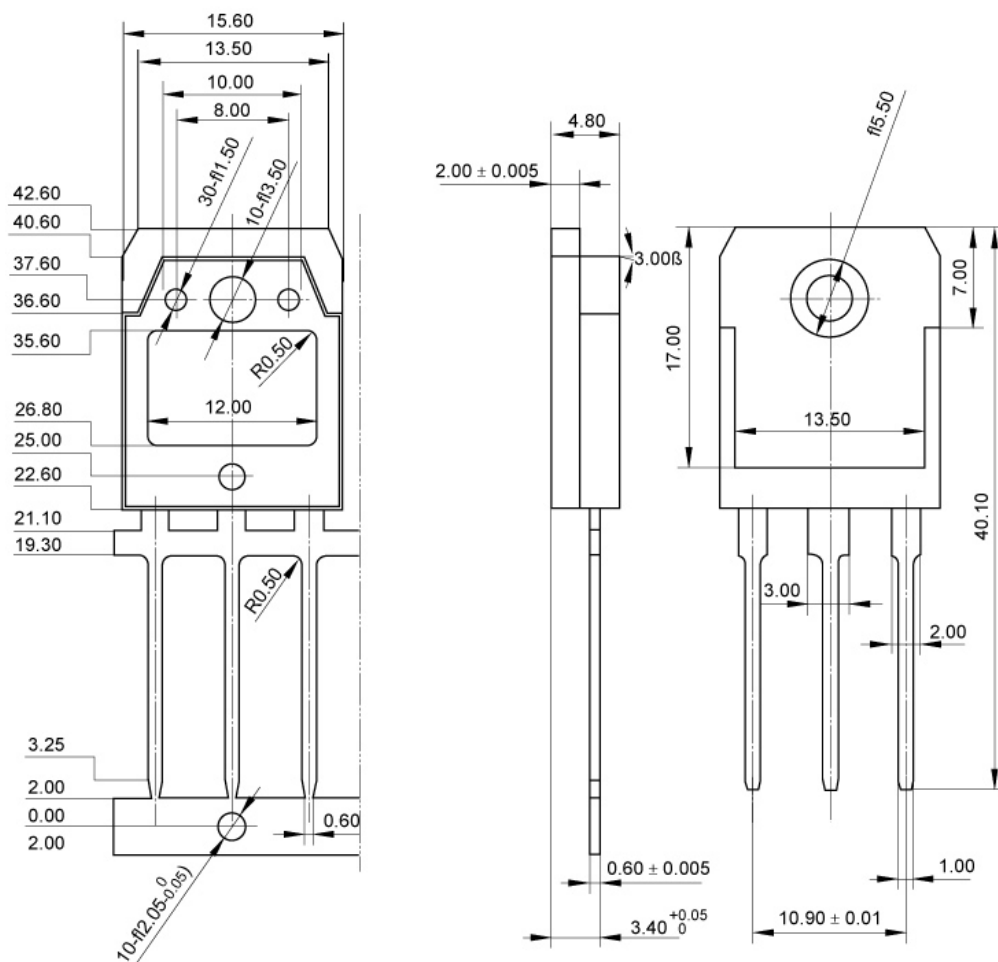


Fig.2 outline dimensions